

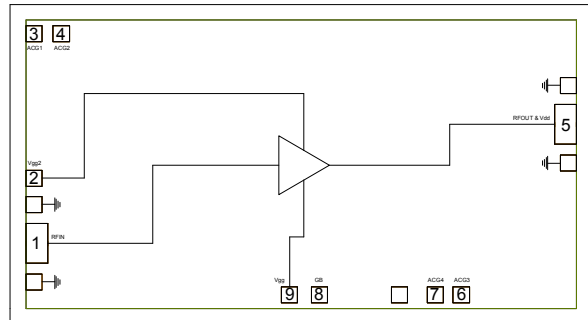
Features

- ▶ Ultra wideband performance
- ▶ Positive gain slope
- ▶ High output power
- ▶ Low noise figure
- ▶ Small die size

Description

The CMD192 is wideband GaAs MMIC distributed amplifier die which operates from DC to 20 GHz. The amplifier delivers greater than 19 dB of gain with a corresponding output 1 dB compression point of +24.5 dBm and noise figure of 1.9 dB at 10 GHz. The CMD192 is a 50 ohm matched design which eliminates the need for RF port matching. The CMD192 offers full passivation for increased reliability and moisture protection. This amplifier is the perfect alternative to higher cost hybrid amplifiers.

Functional Block Diagram



Note: Vgg2 is optional for gain control

Electrical Performance - $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F = 10\text{ GHz}$

| Parameter | Min | Typ | Max | Units |
|--------------------|---------|------|-----|-------|
| Frequency Range | DC - 20 | | | GHz |
| Gain | | 19.5 | | dB |
| Noise Figure | | 1.9 | | dB |
| Input Return Loss | | 25 | | dB |
| Output Return Loss | | 15 | | dB |
| Output P1dB | | 24.5 | | dBm |
| Supply Current | | 200 | | mA |



CMD192

DC-20 GHz Distributed Driver Amplifier

Specifications

Absolute Maximum Ratings

| Parameter | Rating |
|--------------------------------------|---------------|
| Drain Voltage, V _{dd} | 10 V |
| Gate Voltage, V _{gg} | -4 to 0 V |
| RF Input Power | +23 dBm |
| Channel Temperature, T _{ch} | 150 °C |
| Power Dissipation, P _{diss} | 2.8 W |
| Thermal Resistance, Θ_{JC} | 23.2 °C/W |
| Operating Temperature | -55 to 85 °C |
| Storage Temperature | -55 to 150 °C |

Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

Recommended Operating Conditions

| Parameter | Min | Typ | Max | Units |
|-----------------|------|------|------|-------|
| V _{dd} | 5.0 | 8.0 | 10.0 | V |
| I _{dd} | | 200 | | mA |
| V _{gg} | -4.0 | -1.0 | 0 | V |

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

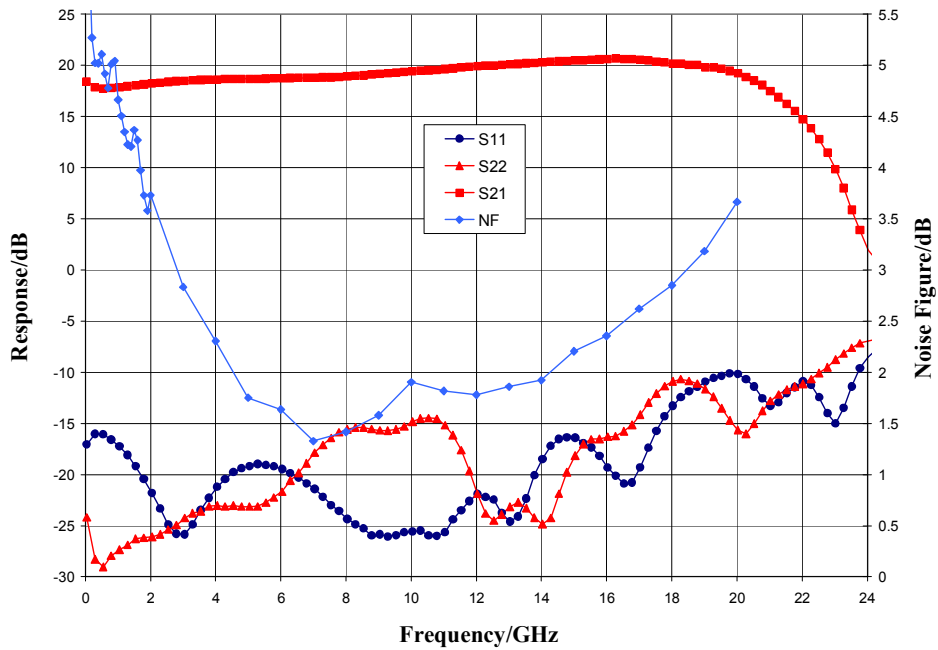
Electrical Specifications, V_{dd} = 8.0 V, V_{gg} = -1.0 V, T_A = 25 °C

| Parameter | Min | Typ | Max | Min | Typ | Max | Units |
|--------------------------------------|---------|-------|-----|---------|-------|-----|-------|
| Frequency Range | DC - 10 | | | 10 - 20 | | | GHz |
| Gain | 15.5 | 18.5 | | 17 | 20 | | dB |
| Noise Figure | | 2 | | | 2.5 | | dB |
| Input Return Loss | | 20 | | | 15 | | dB |
| Output Return Loss | | 20 | | | 15 | | dB |
| Output P1dB | 22 | 24.5 | | 19 | 22 | | dBm |
| Output IP3 | | 31 | | | 29 | | dBm |
| Supply Current | 140 | 200 | 260 | 140 | 200 | 260 | mA |
| Gain Temperature Coefficient | | 0.012 | | | 0.02 | | dB/°C |
| Noise Figure Temperature Coefficient | | 0.006 | | | 0.009 | | dB/°C |

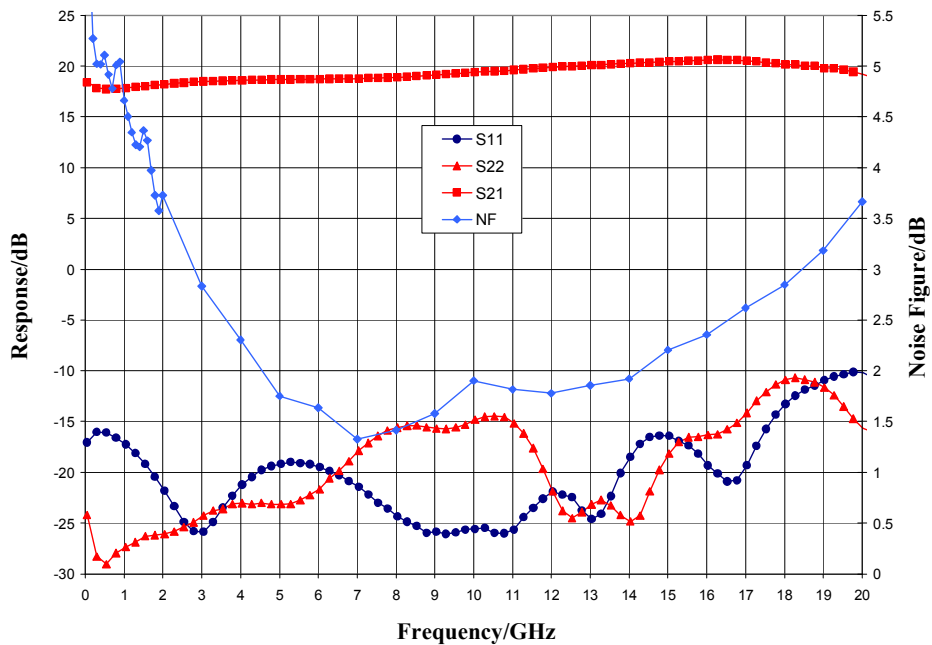
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Typical Performance

Broadband Performance, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$, $I_{dd} = 170\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



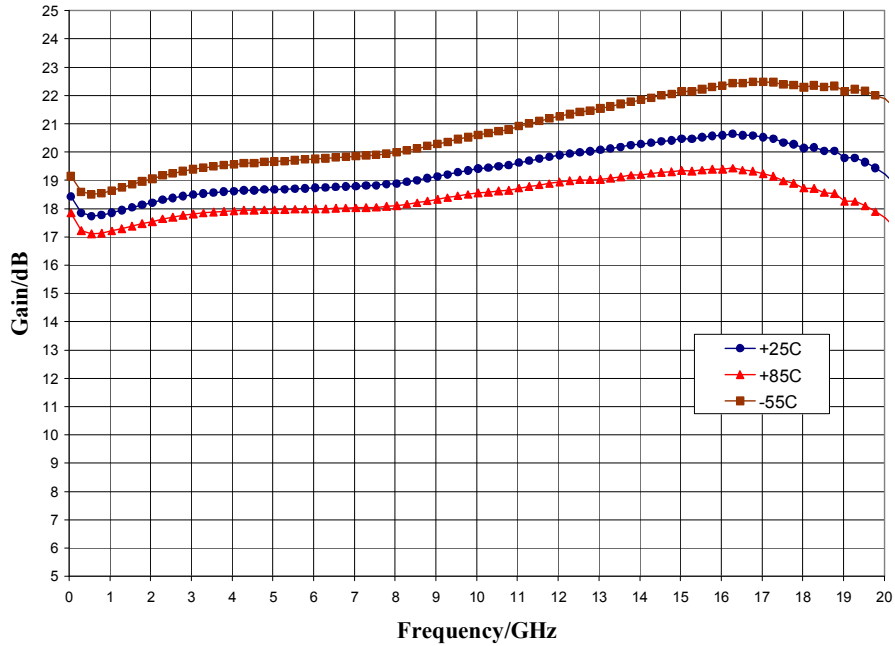
Narrow-band Performance, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$, $I_{dd} = 170\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



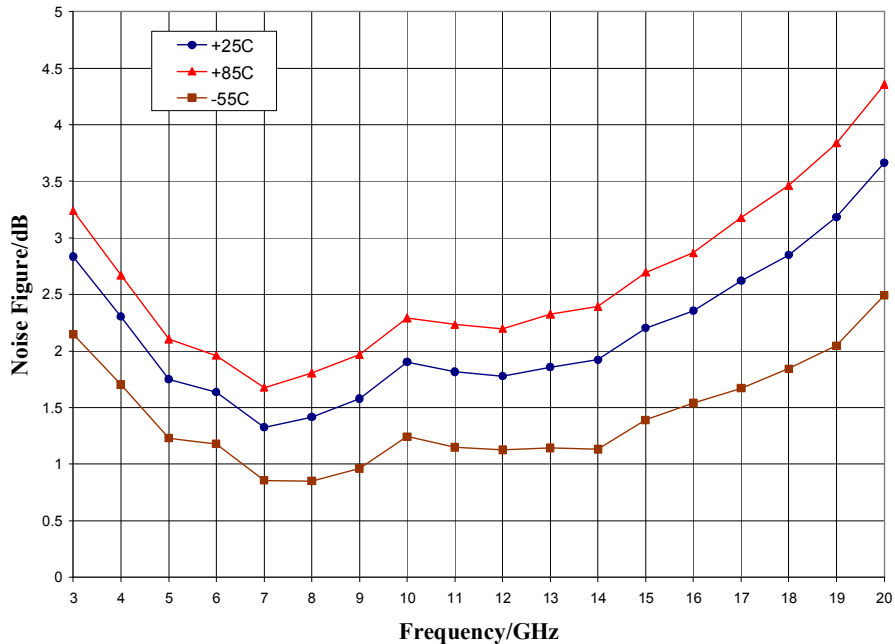
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Typical Performance

Gain vs. Temperature, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$



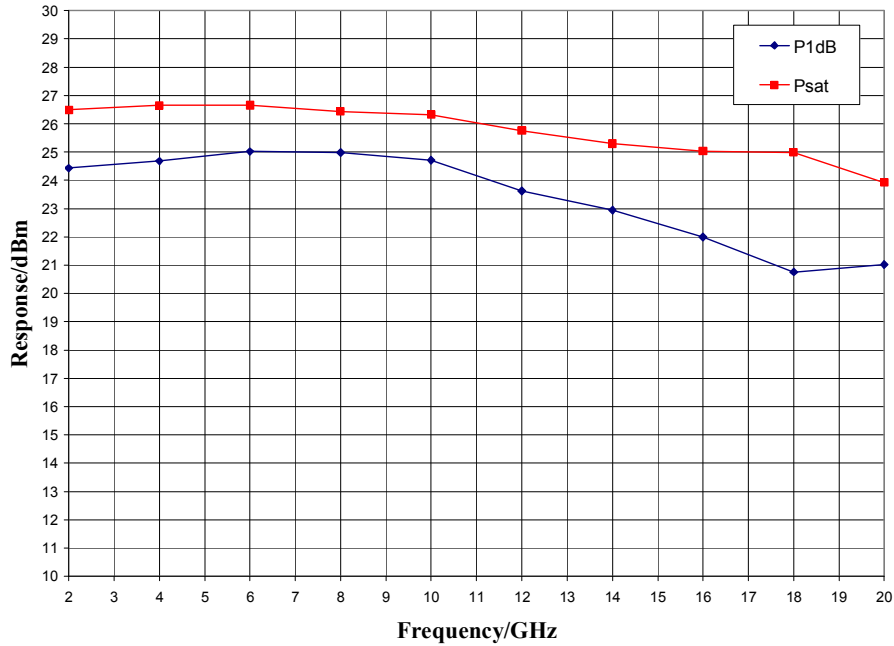
Noise Figure vs. Temperature, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$



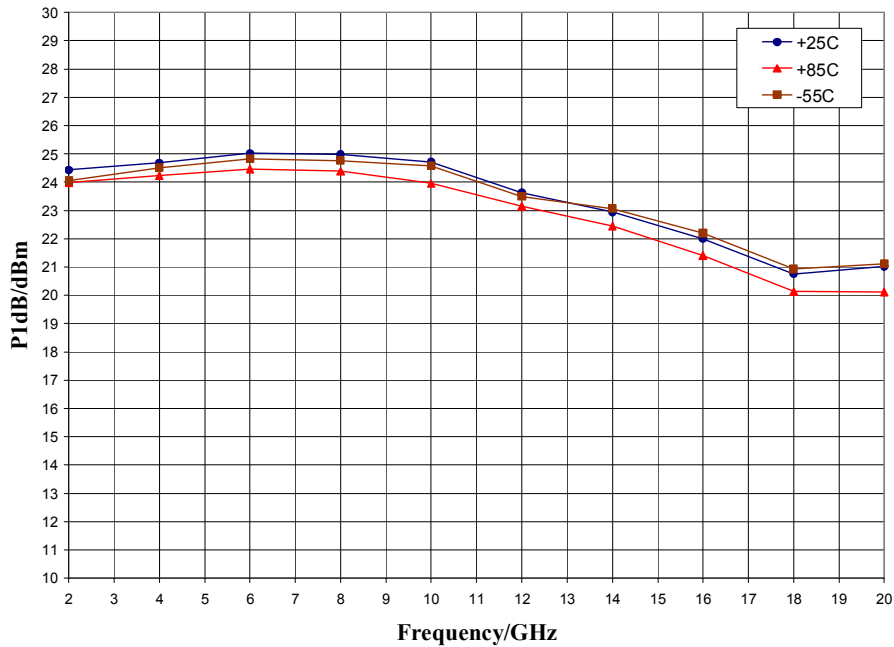
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Typical Performance

Output Power, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$



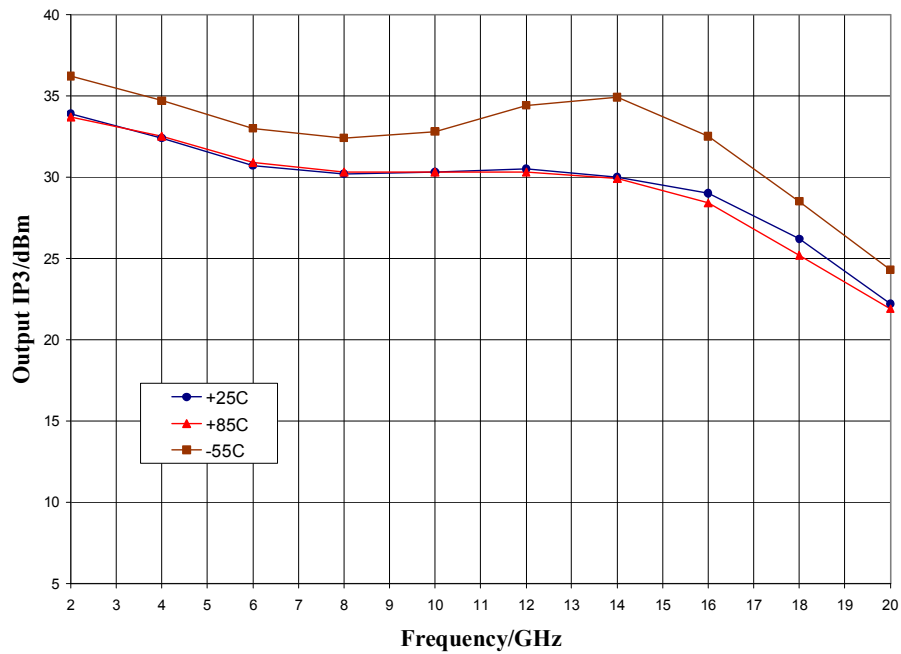
P1dB vs. Temperature, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$



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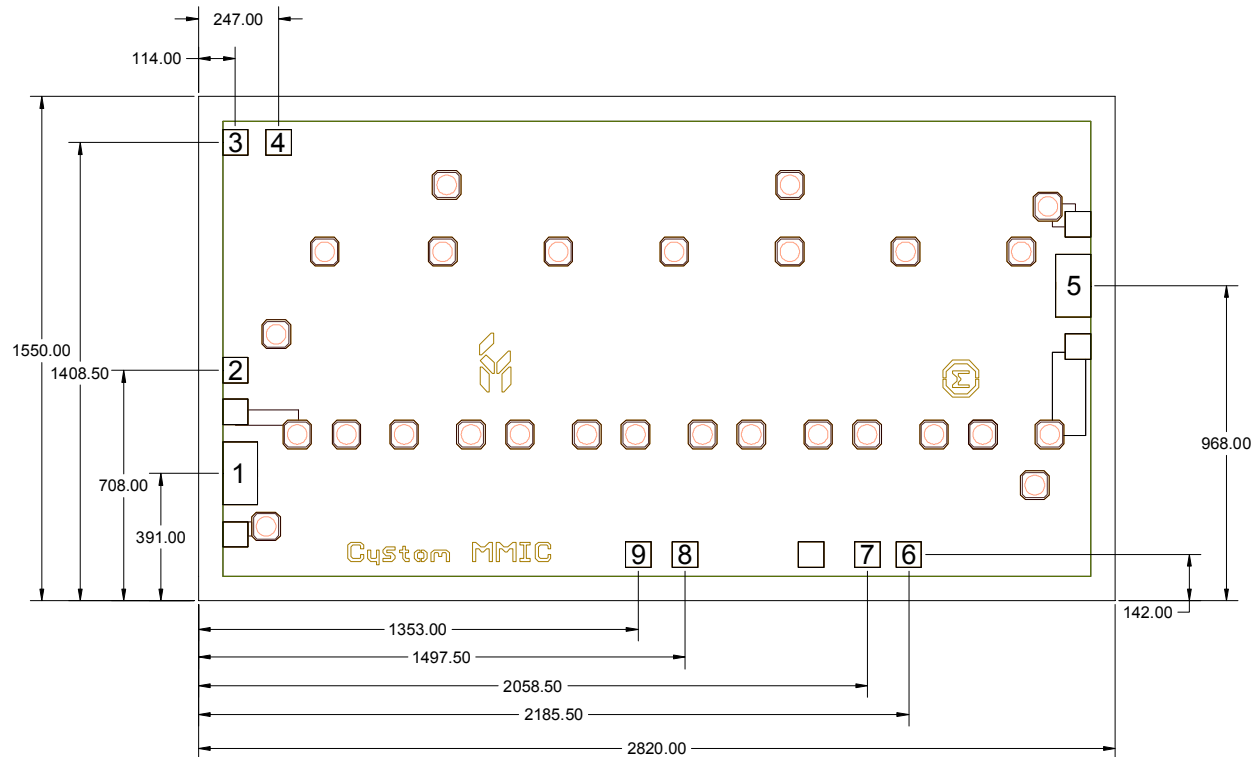
Typical Performance

Output IP3 vs. Temperature, $V_{dd} = 8.0\text{ V}$, $V_{gg} = -1.0\text{ V}$



Mechanical Information

Die Outline (all dimensions in microns)

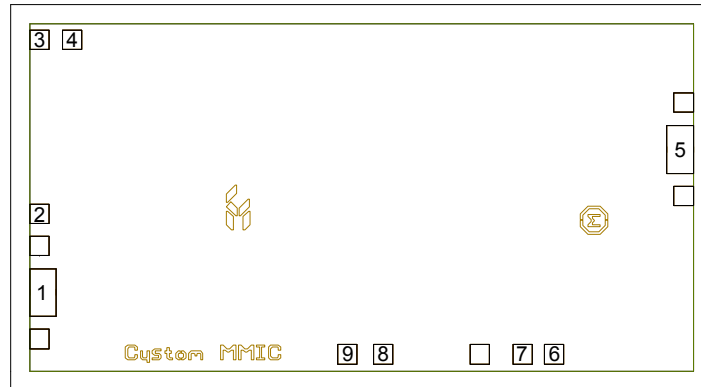


Notes:

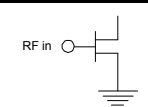
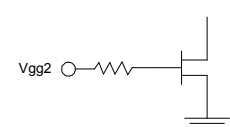
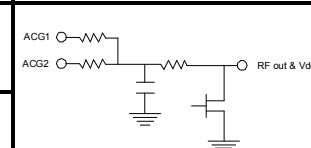
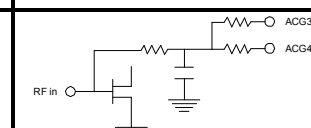



1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads (2, 3, 4, 6, 7, 8, 9) are 78 microns square
6. RF bond pads (1, 5) are 108 x 193 microns

Pad Description

Pad Diagram



Functional Description

| Pad | Function | Description | Schematic |
|----------|--------------|---|---|
| 1 | RF in | 50 ohm matched input |  |
| 2 | Vgg2 | Optional supply voltage for gain control Decoupling and bypass caps required |  |
| 3, 4 | ACG1, 2 | Low frequency termination. Attach bypass capacitor per application circuit |  |
| 5 | RF out & Vdd | Power supply voltage and 50 ohm matched output | |
| 6, 7 | ACG3, 4 | Low frequency termination. Attach bypass capacitor per application circuit |  |
| 8 | GB | Connect to DC ground |  |
| 9 | Vgg | Power supply voltage Decoupling and bypass caps required |  |
| Backside | Ground | Connect to RF / DC ground |  |

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Applications Information

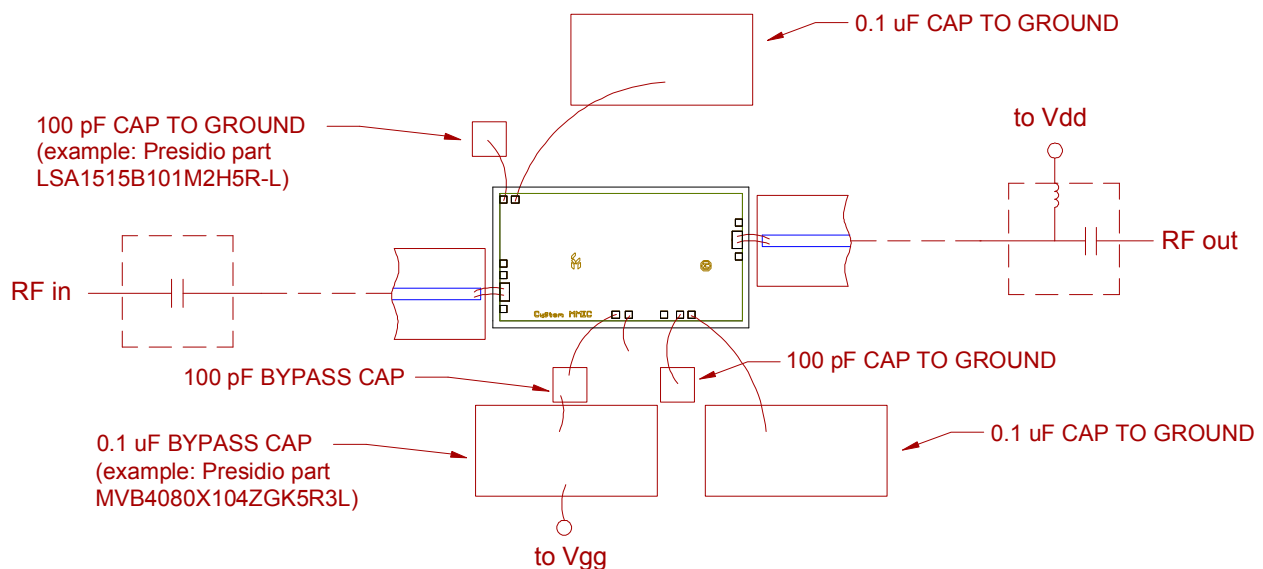
Assembly Guidelines

The backside of the CMD192 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.